

NTD6415ANL

N-Channel Power MOSFET 100 V, 23 A, 56 mΩ, Logic Level

Features

- Low $R_{DS(on)}$
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	100	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	23
		$T_C = 100^\circ\text{C}$	16
Power Dissipation	P_D	83	W
Pulsed Drain Current	I_{DM}	80	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	23	A
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50\text{ Vdc}$, $V_{GS} = 10\text{ Vdc}$, $I_{L(pk)} = 23\text{ A}$, $L = 0.3\text{ mH}$, $R_G = 25\ \Omega$)	E_{AS}	79	mJ
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds	T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) – Steady State	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	39	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

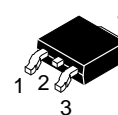
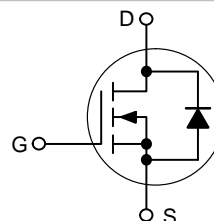
1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).



ON Semiconductor®

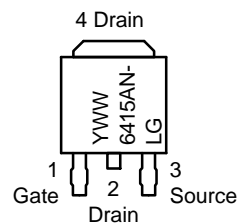
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
100 V	56 mΩ @ 4.5 V	23 A
	52 mΩ @ 10 V	



DPAK
CASE 369AA
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



6415ANL = Device Code
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NTD6415ANL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA V _{GS} = 0 V, I _D = 250 μA, T _J = -40°C	100 92			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			115		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V			1.0 100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		2.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			4.8		mV/°C
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A V _{GS} = 10 V, I _D = 10 A		44 43	56 52	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 5.0 V, I _D = 10 A		24		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		1024		pF
Output Capacitance	C _{OSS}			156		
Reverse Transfer Capacitance	C _{RSS}			70		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 80 V, I _D = 23 A		20		nC
Threshold Gate Charge	Q _{G(TH)}			1.1		
Gate-to-Source Charge	Q _{GS}			3.1		
Gate-to-Drain Charge	Q _{GD}			14		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 80 V, I _D = 23 A		35		nC

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DD} = 80 V, I _D = 23 A, R _G = 6.1 Ω		11		ns
Rise Time	t _r			91		
Turn-Off Delay Time	t _{d(off)}			40		
Fall Time	t _f			71		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 23 A	T _J = 25°C T _J = 125°C	0.87 0.74	1.2	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 23 A		64		ns
Charge Time	T _a			40		
Discharge Time	T _b			24		
Reverse Recovery Charge	Q _{RR}			152		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTD6415ANLT4G	DPAK (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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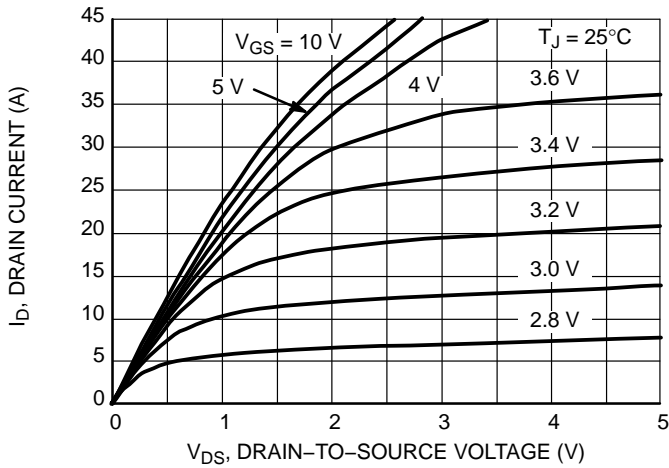


Figure 1. On-Region Characteristics

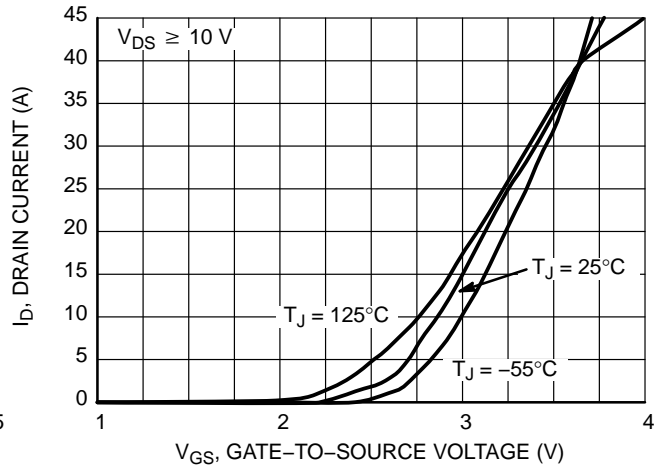


Figure 2. Transfer Characteristics

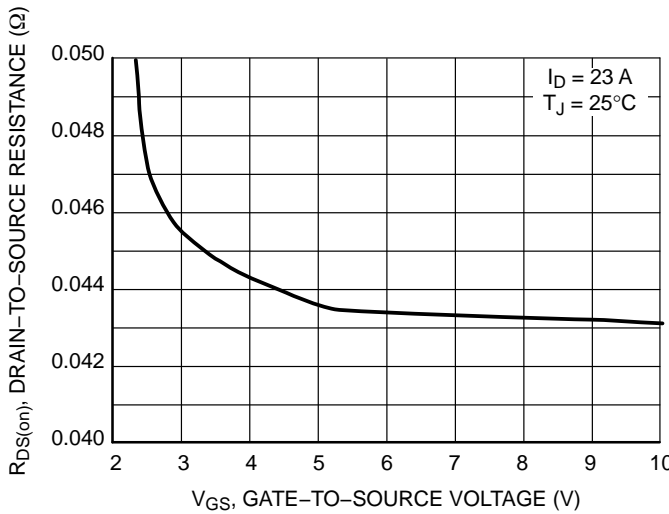


Figure 3. On-Region versus Gate Voltage

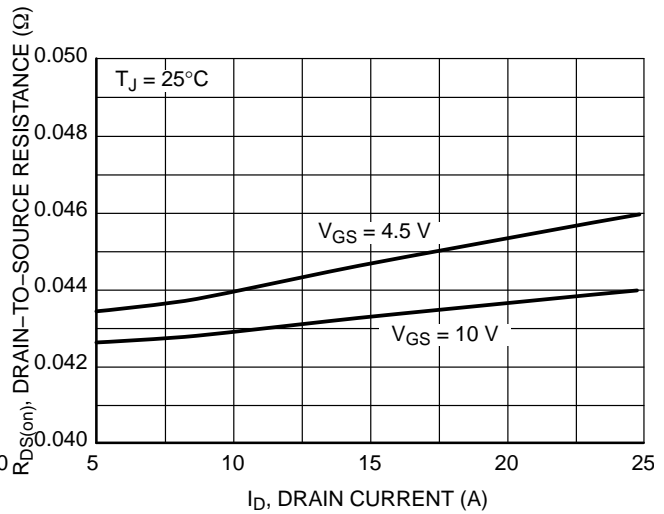


Figure 4. On-Resistance versus Drain Current and Gate Voltage

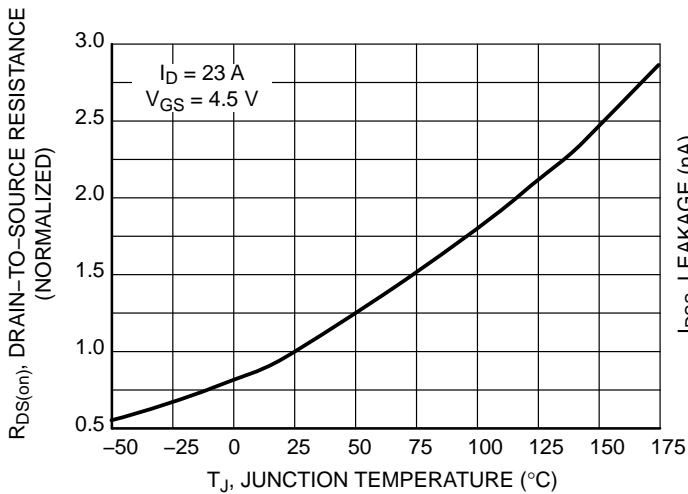


Figure 5. On-Resistance Variation with Temperature

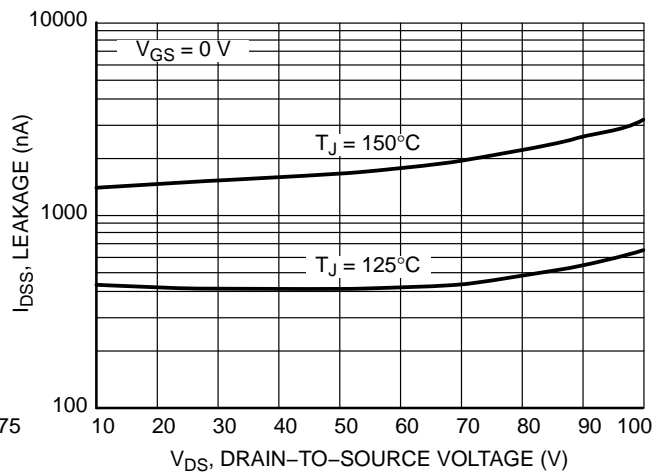


Figure 6. Drain-to-Source Leakage Current versus Voltage

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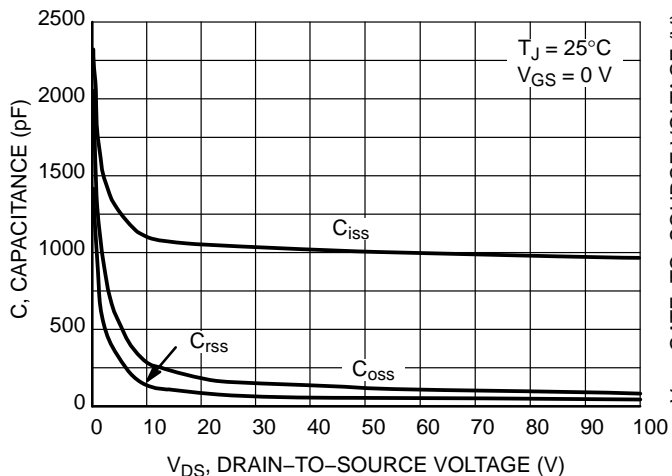


Figure 7. Capacitance Variation

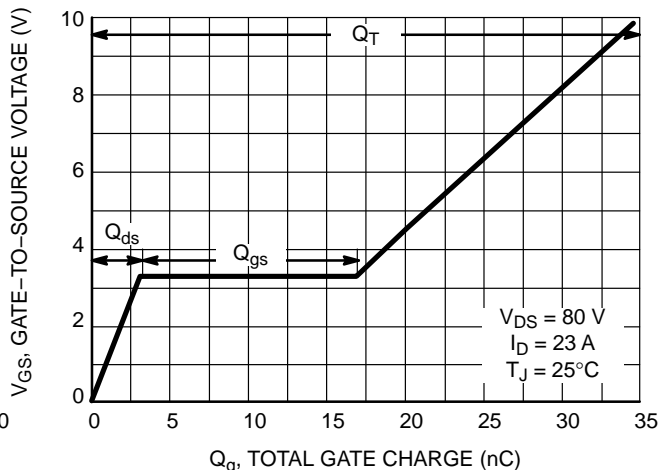


Figure 8. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

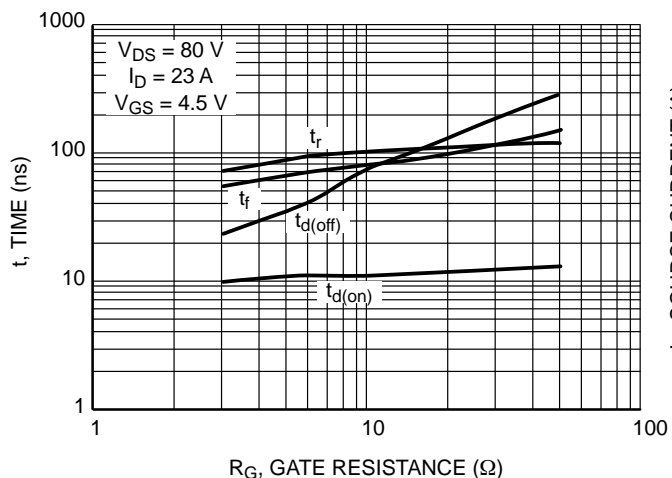


Figure 9. Resistive Switching Time Variation versus Gate Resistance

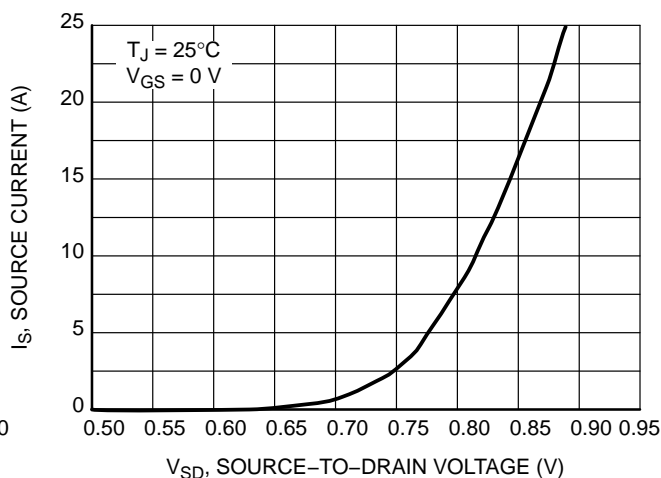


Figure 10. Diode Forward Voltage versus Current

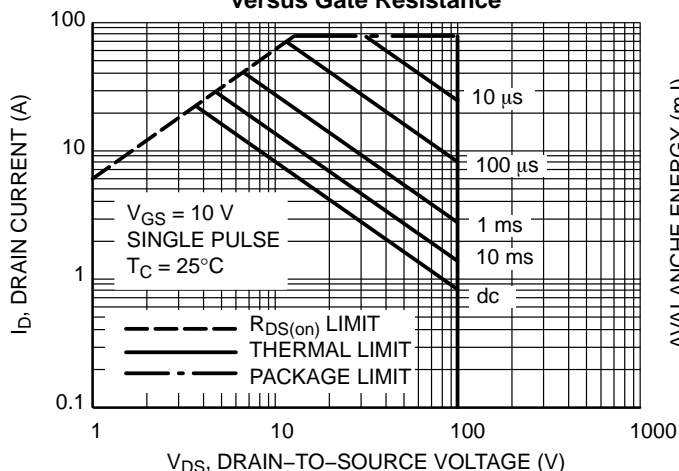


Figure 11. Maximum Rated Forward Biased Safe Operating Area

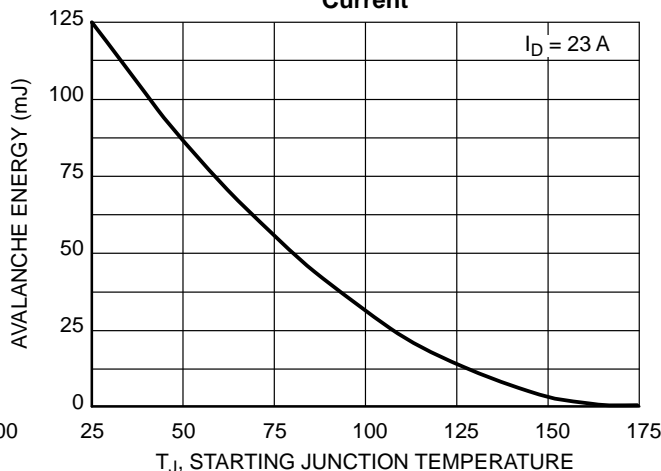


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

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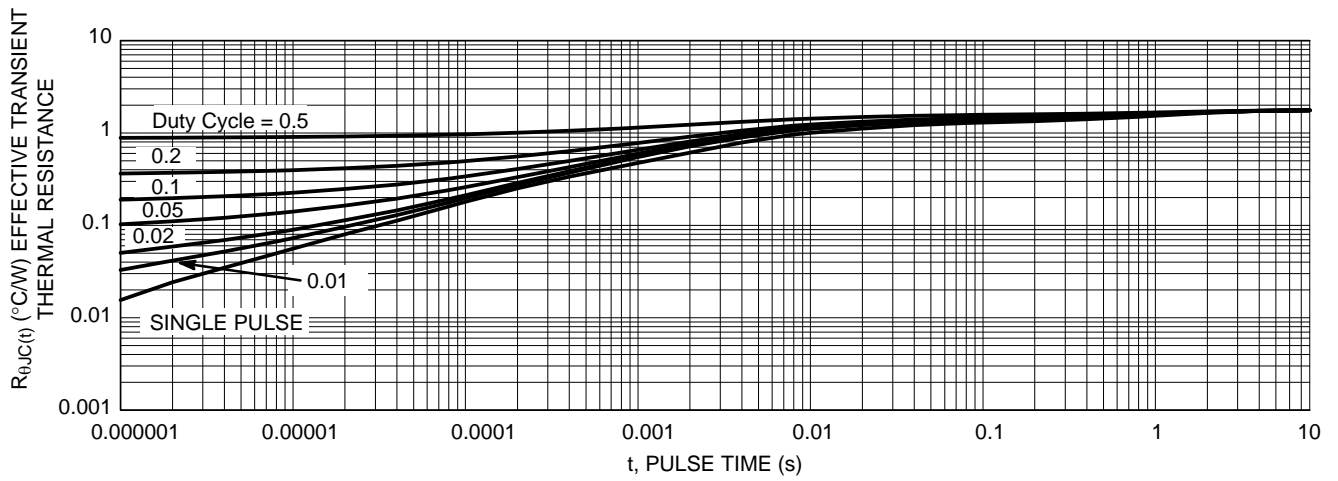
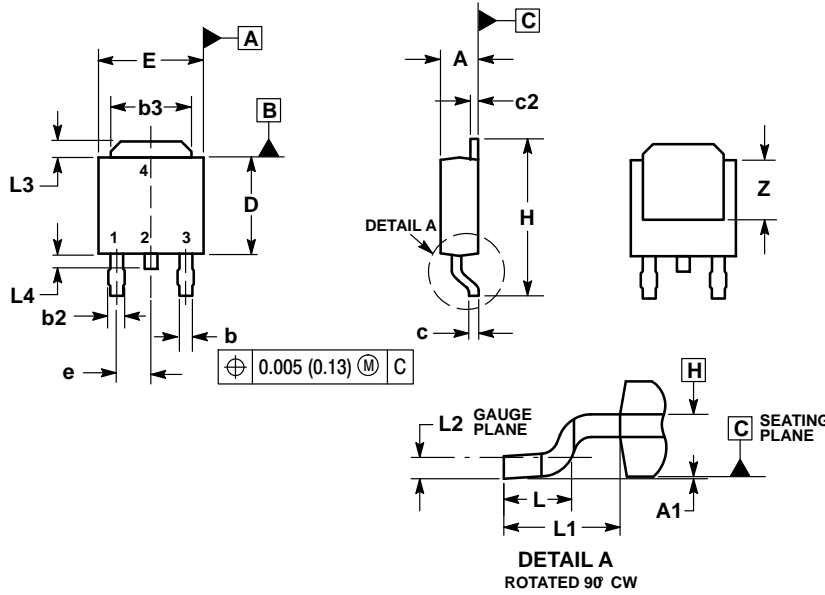


Figure 13. Thermal Response

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PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369AA ISSUE B

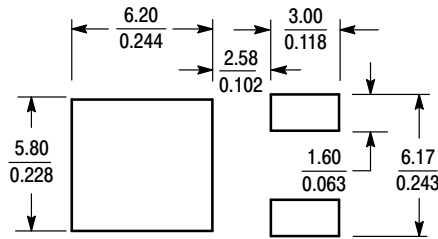


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 ($\frac{\text{mm}}{\text{inches}}$)

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.